

In the Abstract:

Please **replace** the paragraph at **page 17 lines 2 to 12**, with a replacement paragraph amended as follows:

A method of processing a surface of a nitride semiconductor crystal, wherein a surface of a nitride semiconductor crystal ~~[[ $\langle 11 \rangle$ ]]~~ is brought into contact with a liquid containing at least Na, Li or Ca as a processing ~~solution~~ ~~(15)~~. solution. In the method, the processing solution ~~[[ $\langle 15 \rangle$ ]]~~ can be a liquid containing at least Na, having an Na content of 5-95 mol%. The processing solution ~~[[ $\langle 15 \rangle$ ]]~~ can be a liquid containing at least Li, having an Li content of 5-100 mol%. A nitride semiconductor crystal having a maximum depth of a surface scratch of at most 0.01  $\mu\text{m}$  or an average thickness of a damaged layer of at most 2  $\mu\text{m}$ . Consequently, a method of processing a surface of a nitride semiconductor crystal with a decreased depth of a surface scratch or a decreased thickness of a damaged layer, and a nitride semiconductor crystal obtained with the method can be provided.

**[REMARKS FOLLOW ON NEXT PAGE]**